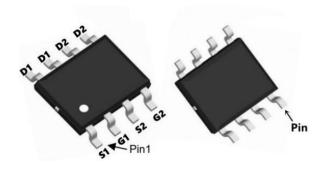
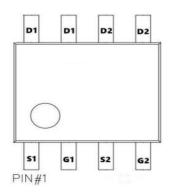


-60V P+P-Channel Enhancement Mode MOSFET

Description

The SX6V06S uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

 $V_{DS} = -60V I_{D} = -6A$

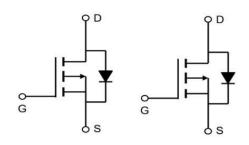
 $R_{DS(ON)} < 85m\Omega$ @ $V_{GS}=10V$

Application

Brushless motor

Load switch

Uninterruptible power supply



Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|--------------------|---|------------|------------|
| V _D s | Drain-Source Voltage | -60 | V |
| Vgs | Gate-Source Voltage | ±20 | V |
| l o@Tc=25℃ | Continuous Drain Current, V _{GS} @ -10V ¹ | -6 | Α |
| lo@Tc=100°C | Continuous Drain Current, V _{GS} @ -10V ¹ | -4.3 | А |
| Ірм | Pulsed Drain Current ² | -26 | Α |
| EAS | Single Pulse Avalanche Energy³ | 29.8 | mJ |
| las | Avalanche Current | -24.4 | Α |
| P @Tc=25°C | Total Power Dissipation ⁴ | 31.3 | W |
| Тѕтс | Storage Temperature Range | -55 to 150 | $^{\circ}$ |
| TJ | Operating Junction Temperature Range | -55 to 150 | $^{\circ}$ |
| Reja | Thermal Resistance Junction-Ambient ¹ | 85 | °C/W |
| Rejc | Thermal Resistance Junction-Case ¹ | 40 | °C/W |

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-60V P+P-Channel Enhancement Mode MOSFET

P-Channel Electrical Characteristics (TJ =25 ℃, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit | |
|-----------|--|--|------|-------|------|------|--|
| BVDSS | Drain-Source Breakdown Voltage | Vgs=0V , In=-250uA | -60 | -66 | | V | |
| △BVDSS/△T | BV _{DSS} Temperature Coefficient | Reference to 25°C , I _D =-1mA | | -0.03 | | V/℃ | |
| RDS(ON) | Static Drain-Source On-Resistance ² | Vgs=-10V , Ip=-3A | | 65 | 85 | mΩ | |
| | | V _G S=-4.5V , I _D =-2A | | 80 | 100 | | |
| VGS(th) | Gate Threshold Voltage | Vgs=Vds , ld =-250uA | -1.2 | 1.75 | -2.5 | V | |
| IDSS | Drain-Source Leakage Current | Vɒs=-48V , Vgs=0V , Tɹ=25℃ | | | 1 | uA | |
| | | V _{DS} =-48V , V _{GS} =0V , T _J =55℃ | | | 5 | uA | |
| IGSS | Gate-Source Leakage Current | Vgs=±20V , Vps=0V | | | ±100 | nA | |
| gfs | Forward Transconductance | VDS=-5V , ID=-3A | | 8.5 | | S | |
| Qg | Total Gate Charge (-4.5V) | | | 12.1 | | | |
| Qgs | Gate-Source Charge | VDS=-48V , VGS=-4.5V , ID=-3A | | 2.2 | | nC | |
| Qgd | Gate-Drain Charge | | | 6.3 | | | |
| Td(on) | Turn-On Delay Time | | | 9.2 | | | |
| Tr | Rise Time | V _{DD} =-15V , V _{GS} =-10V , R _G =3.3 , | | 20.1 | | | |
| Td(off) | Turn-Off Delay Time | b=-1A | | 46.7 | | ns | |
| Tf | Fall Time | | | 9.4 | | | |
| Ciss | Input Capacitance | | | 1137 | | | |
| Coss | Output Capacitance | V _{DS} =-15V , V _{GS} =0V , f=1MHz | | 76 | | pF | |
| Crss | Reverse Transfer Capacitance | | | 50 | | | |
| IS | Continuous Source Current ^{1,5} | V _G =V _D =0V , Force Current | | | -13 | Α | |
| VSD | Diode Forward Voltage ² | Vgs=0V , Is=-1A , Tյ=25℃ | | | -1.2 | V | |

Note

- 1. The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$
- $3\,{}^{\backprime}$ The power dissipation is limited by $150\,{}^{\circ}\mathrm{C}\textsc{junction}$ temperature
- 4. The data is theoretically the same as I D and I DM, in real applications, should be limited by total power dissipation.

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Typical Characteristics

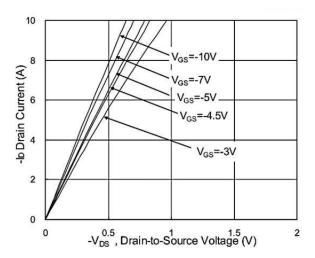


Fig.1 Typical Output Characteristics

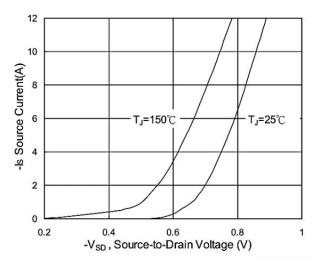


Fig.3 Forward Characteristics of Reverse

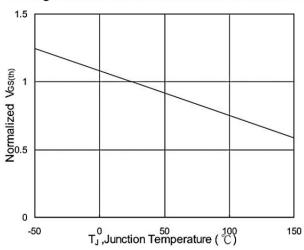


Fig.5 Normalized $V_{\text{GS(th)}}$ v.s T_{J}

3

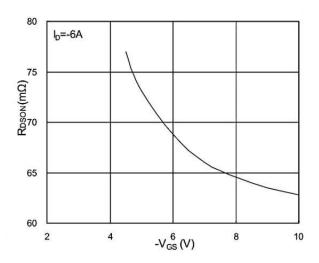


Fig.2 On-Resistance v.s Gate-Source

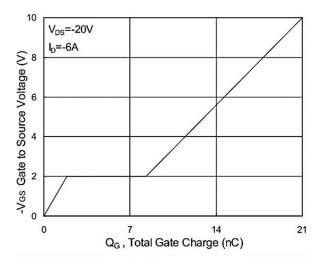


Fig.4 Gate-Charge Characteristics

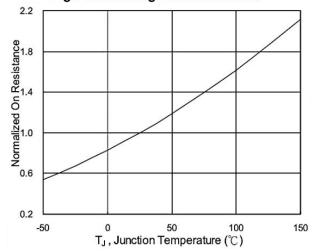
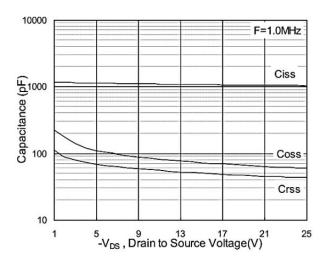
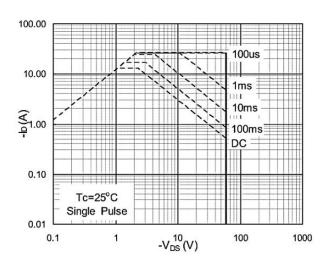


Fig.6 Normalized R_{DSON} v.s T_J



Typical Characteristics





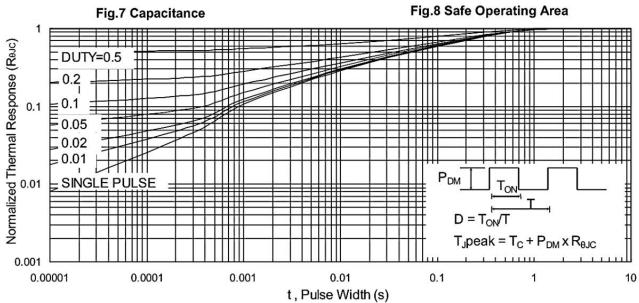


Fig.9 Normalized Maximum Transient Thermal Impedance

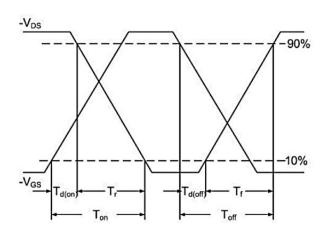


Fig.10 Switching Time Waveform

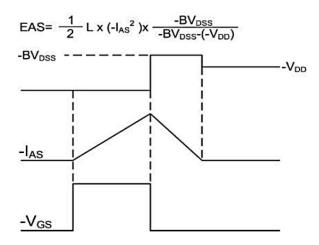
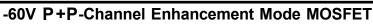
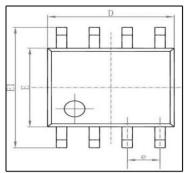


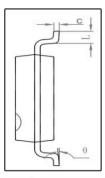
Fig.11 Unclamped Inductive Switching Waveform

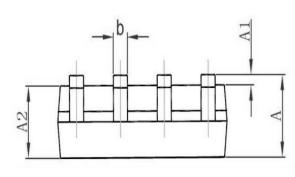




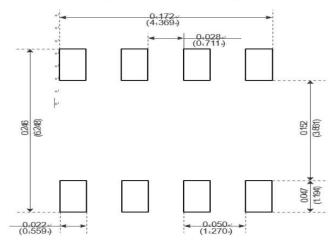
Package Mechanical Data-SOP-8L







| Cl 1 | Dimensions In | n Millimeters | Dimensions | In Inches |
|--------|---------------|---------------|------------|-----------|
| Symbol | Min | Max | Min | Max |
| Α | 1. 350 | 1. 750 | 0. 053 | 0.069 |
| A1 | 0. 100 | 0. 250 | 0. 004 | 0.010 |
| A2 | 1. 350 | 1. 550 | 0. 053 | 0.061 |
| b | 0. 330 | 0. 510 | 0. 013 | 0. 020 |
| С | 0. 170 | 0. 250 | 0.006 | 0.010 |
| D | 4. 700 | 5. 100 | 0. 185 | 0. 200 |
| E | 3. 800 | 4. 000 | 0. 150 | 0. 157 |
| E1 | 5. 800 | 6. 200 | 0. 228 | 0. 244 |
| е | 1. 270 | (BSC) | 0.050 | (BSC) |
| L | 0.400 | 1. 270 | 0. 016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



Recommended Minimum Pads

Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|--------|---------|----------|
| TAPING | SOP-8L | | 3000 |

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